

## GENERAL DESCRIPTION

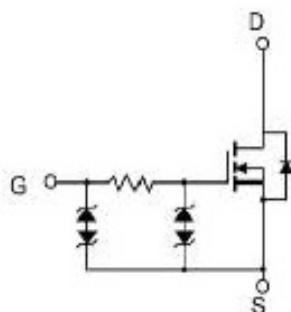
The HM2302BSR is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance.

## FEATURES

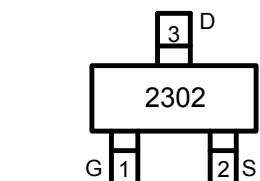
- $R_{DS(ON)} = 270 \text{ m}\Omega @ V_{GS} = 4.5V$
- $R_{DS(ON)} = 330 \text{ m}\Omega @ V_{GS} = 2.5V$
- $R_{DS(ON)} = 450 \text{ m}\Omega @ V_{GS} = 1.8V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- Capable doing Cu wire bonding

## APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- Load Switch



B!7\ UbbY



Marking and pin Assignment



SOT-523 top view

## Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ Unless Otherwise Noted)

Parameter	Symbol	Maximum Ratings	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V

**Absolute Maximum Ratings (TA=25°C Unless Otherwise Noted)**

Parameter	Symbol	Maximum Ratings	Unit
Drain-Source Voltage	VDS	20	V
Gate-Source Voltage	VGS	±8	V

**Electrical Characteristics (Tj =25°C Unless Otherwise Specified)**

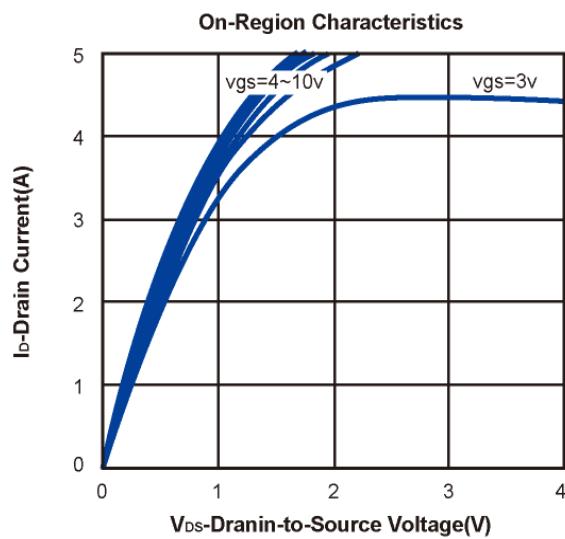
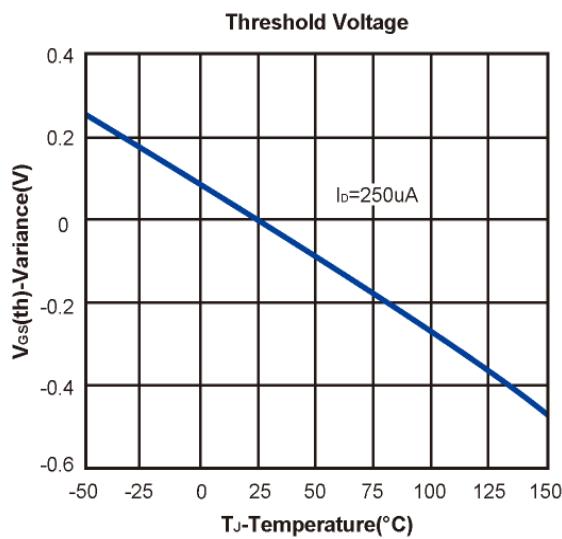
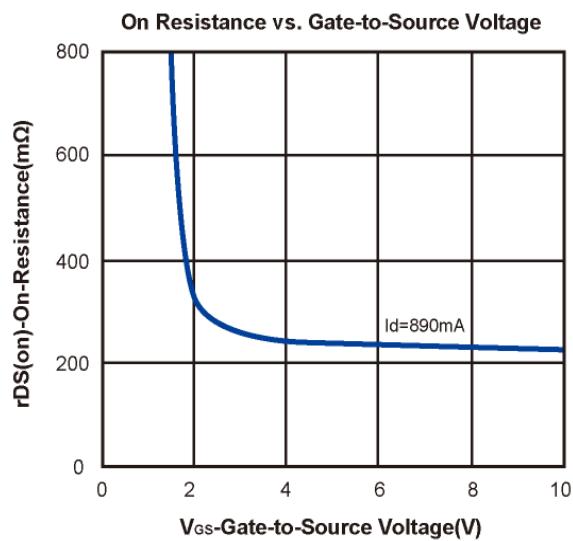
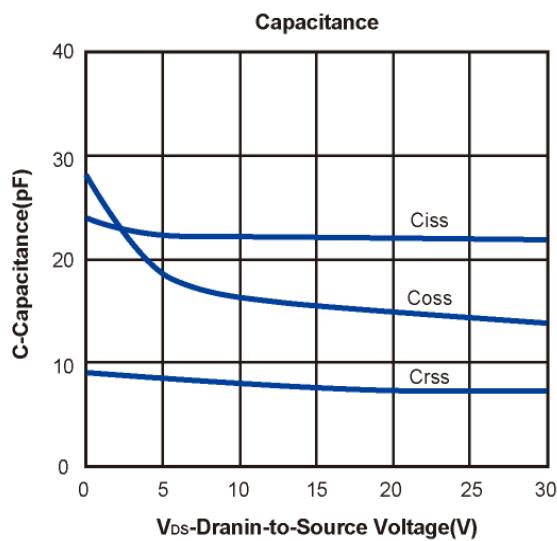
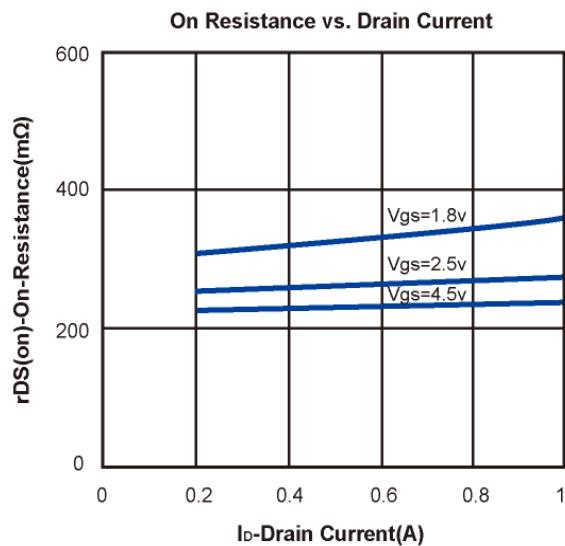
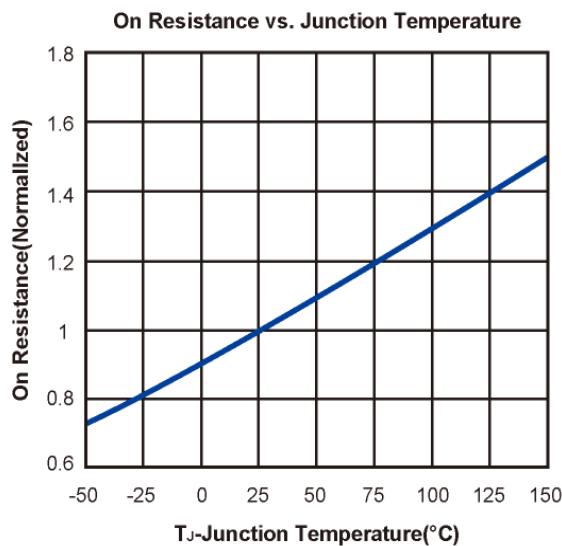
Symbol	Parameter	Limit	Min	Typ	Max	Unit
<b>STATIC</b>						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V, ID=250 μA	20			V
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250 μA	0.45		1.2	V
IGSS	Gate Leakage Current	VDS=0V, VGS=±8V			±10	μA
IDSS	Zero Gate Voltage Drain Current	VDS=20V, VGS=0V			1	μA
RDS(ON)	Drain-Source On-Resistance <sup>a</sup>	VGS=4.5V, ID=890mA		220	270	mΩ
		VGS=2.5V, ID=780mA		260	330	
		VGS=1.8V, ID=700mA		330	450	
VSD	Diode Forward Voltage	Is=350mA, VGS=0V		0.75	1.2	V
<b>DYNAMIC</b>						
Ciss	Input Capacitance	VDS=15V, VGS=0V, f=1MHZ		21		pF
Coss	Output Capacitance			15		
Crss	Reverse Transfer Capacitance			8		
Qg	Total Gate Charge	VDS=25V, VGS=10V, ID=0.22A		6.7		nC
Qgs	Gate-Source Charge			1.2		
Qgd	Gate-Drain Charge			0.9		
td(on)	Turn-On Delay Time	VDD=10V, RL =3Ω VGEN=10V, RG=10Ω		120		ns
tr	Turn-On Rise Time			317		
td(off)	Turn-Off Delay Time			748		
tf	Turn-Off Fall Time			716		

Notes: a. Based on epoxy or solder paste and bond wire Cu wire 1mil×1(S), Cu wire 1mil×1(G) on each die of SOT-523 package.

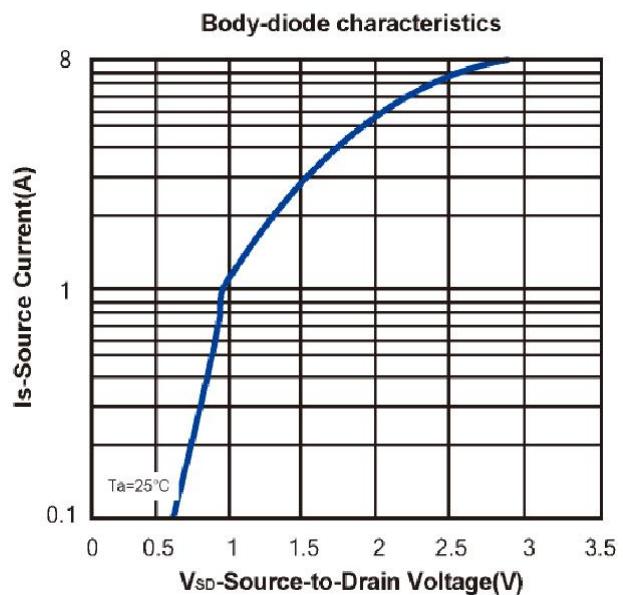
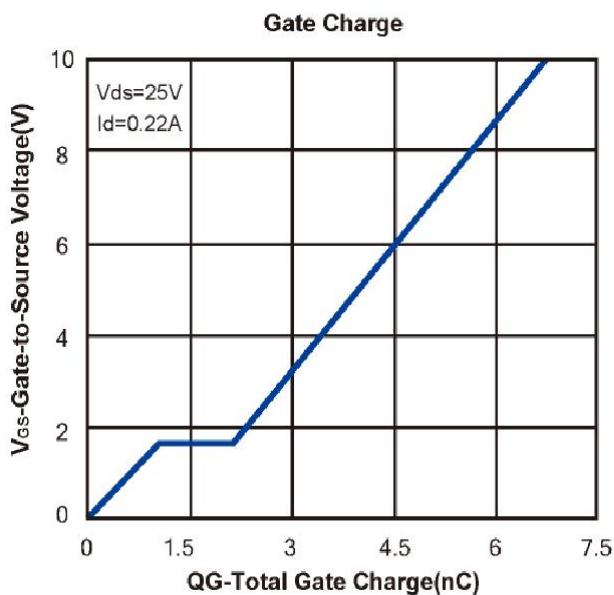
b. Pulse test; pulse width ≤ 300us, duty cycle≤ 2%.

c. Force mos reserves the right to improve product design, functions and reliability without notice.

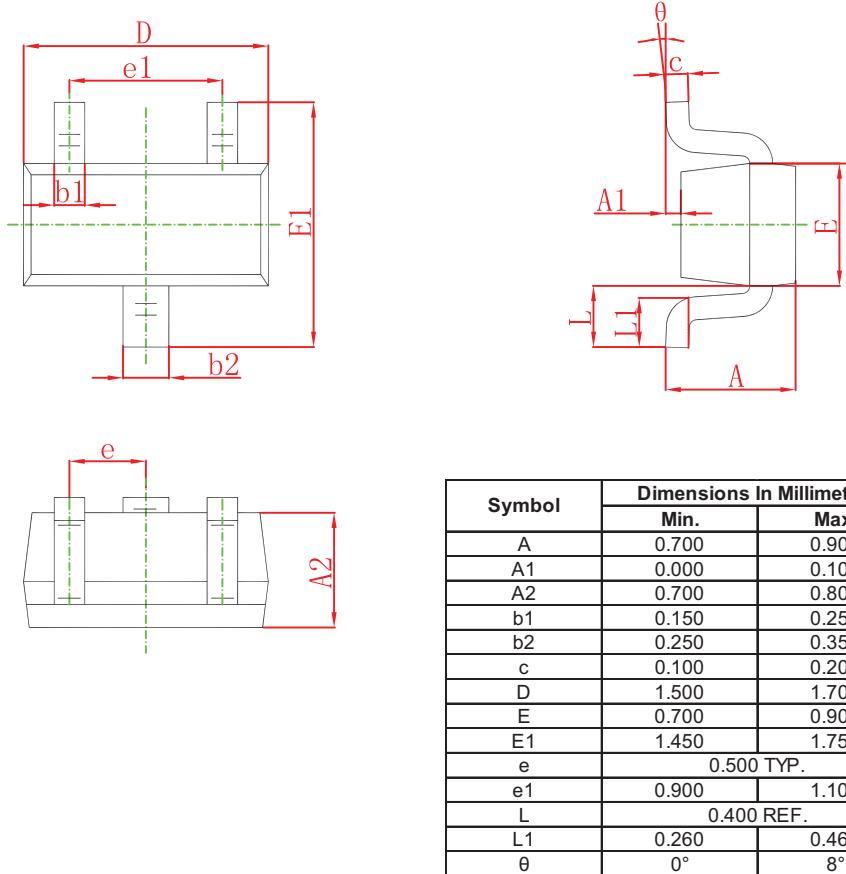
### Typical Characteristics ( $T_J = 25^\circ\text{C}$ Noted)



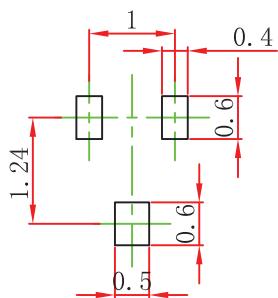
Typical Characteristics ( $T_J = 25^\circ C$  Noted)



## SOT-523 Package Outline Dimensions



## SOT-523 Suggested Pad Layout

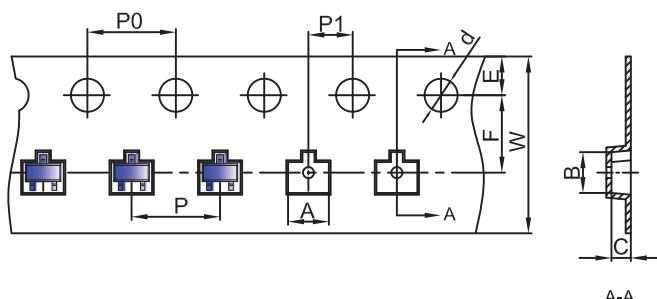


### Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05$ mm.
3. The pad layout is for reference purposes only.

## SOT-523 Tape and Reel

### SOT-523 Embossed Carrier Tape

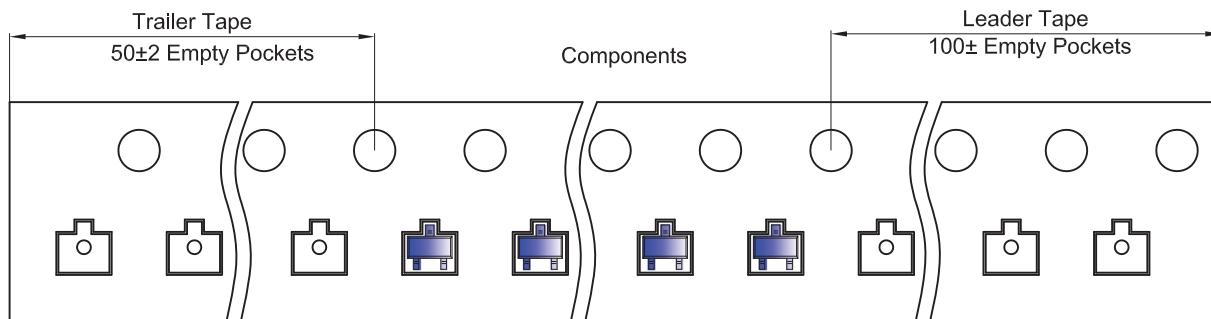


#### Packaging Description:

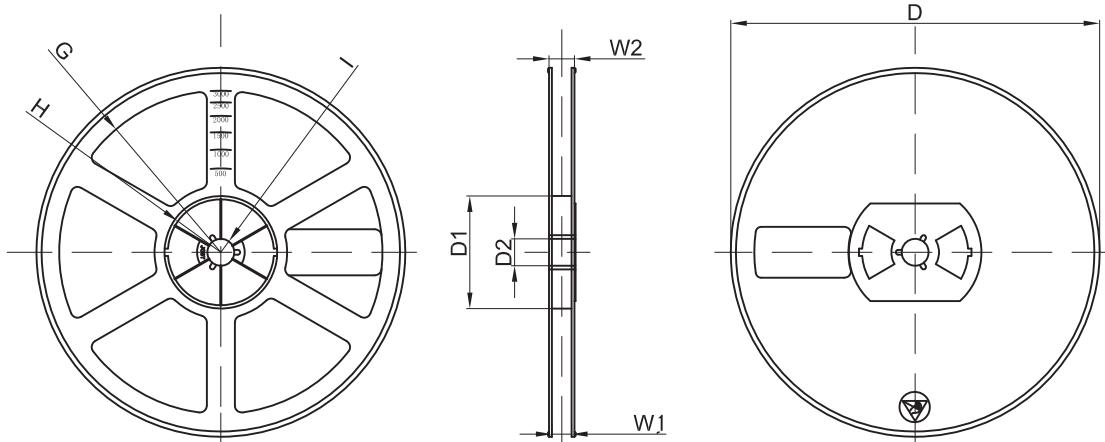
SOT-523 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 17.8cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-523	1.85	1.85	0.875	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

### SOT-523 Tape Leader and Trailer



### SOT-523 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	45,000 pcs	203×203×195	180,000 pcs	438×438×220	